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(71) Applicant (for all designated States except US): **NATIONAL UNIVERSITY OF SINGAPORE** [SG/SG];
10 Kent Ridge Crescent, Singapore 119260 (SG).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **LIAN, Yong** [SG/SG]; c/o National University of Singapore, 10 Kent Ridge Crescent, Singapore 119260 (SG). **YAO, Libin** [CN/SG]; c/o National University of Singapore, 10 Kent Ridge Crescent, Singapore 119260 (SG). **XU, Xiaoyuan**

[CN/SG]; c/o National University of Singapore, 10 Kent Ridge Crescent, Singapore 119260 (SG). **ZOU, Xiaodan** [CN/SG]; c/o National University of Singapore, 10 Kent Ridge Crescent, Singapore 119260 (SG).

(74) Agent: **ELLA CHEONG SPRUSON & FERGUSON (SINGAPORE) PTE LTD**; P.O. Box 1531, Robinson Road Post Office, Singapore 903031 (SG).

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(54) Title: CMOS AMPLIFIER WITH INTEGRATED TUNABLE BAND-PASS FUNCTION

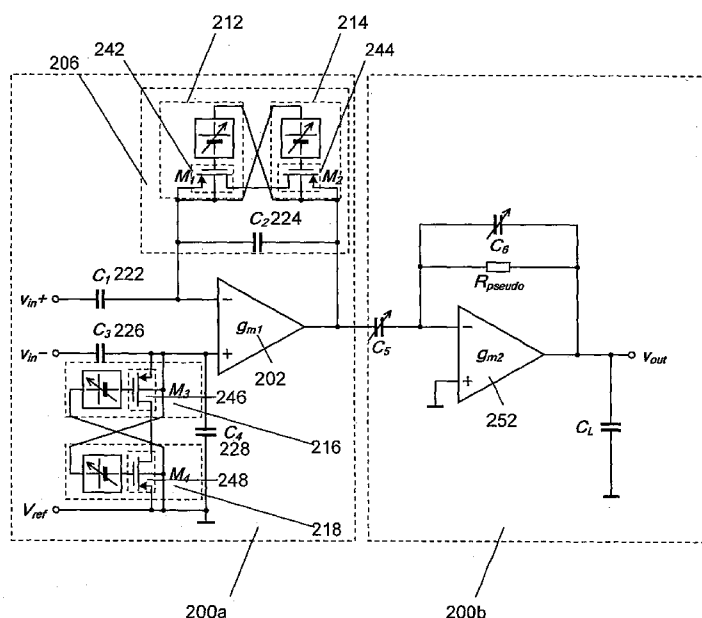


FIG. 2

(57) Abstract: A CMOS amplifier with integrated tunable band-pass function, a tunable active resistor structure, a method of amplifying an input signal and a method of fabricating an amplifier. The tunable active resistor structure comprises two symmetrically cross-coupled transistors.



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